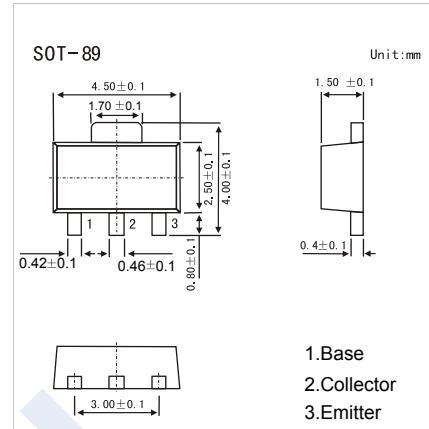


**NPN Transistors****2SC5211****■ Features**

- High voltage  $V_{CEO}=50V$ .
- Small package for mounting.
- Complementary to 2SA1945

**■ Absolute Maximum Ratings  $T_a = 25^\circ C$** 

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	$V_{CBO}$	55	V
Collector - Emitter Voltage	$V_{CEO}$	50	
Emitter - Base Voltage	$V_{EBO}$	4	
Collector Current - Continuous	$I_C$	400	mA
Collector Current - Pulse	$I_{CP}$	600	
Collector Power Dissipation	$P_C$	500	mW
Junction Temperature	$T_J$	150	°C
Storage Temperature Range	$T_{stg}$	-55 to 150	

**■ Electrical Characteristics  $T_a = 25^\circ C$** 

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{CBO}$	$I_C = 100 \mu A, I_E = 0$	55			V
Collector-emitter breakdown voltage	$V_{CEO}$	$I_C = 1 mA, R_{BE} = \infty$	50			
Emitter-base breakdown voltage	$V_{EBO}$	$I_E = 100 \mu A, I_C = 0$	4			
Collector-base cut-off current	$I_{CBO}$	$V_{CB} = 50V, I_E = 0$			1	uA
Emitter cut-off current	$I_{EBO}$	$V_{EB} = 4V, I_C = 0$			1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 200mA, I_B = 10mA$		0.15	0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 200mA, I_B = 10mA$			1.2	
DC current gain	$h_{FE}$	$V_{CE} = 4V, I_C = 100mA$	90		500	
Transition frequency	$f_T$	$V_{CE} = 6V, I_E = -10mA$		150		MHz

**■ Classification of  $h_{FE}$** 

Type	2SC5211-D	2SC5211-E	2SC5211-F
Range	90-180	150-300	250-500
Marking	TD	TE	TF

## NPN Transistors

2SC5211

## ■ Typical Characteristics

